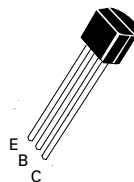


NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

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MPS6601



TO92

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	4	V
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	625	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	25			V	$I_C=100\mu A, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	25			V	$I_C=1mA, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	4			V	$I_E=10\mu A, I_C=0$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=25V, I_E=0$
Collector Cut-Off Current	I_{CES}			0.1	μA	$V_{CE}=25V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.6	V	$I_C=1A, I_B=100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.2	V	$I_C=500mA, V_{CE}=1V^*$
Static Forward Current Transfer Ratio	h_{FE}	50 50 30				$I_C=100mA, V_{CE}=1V^*$ $I_C=500mA, V_{CE}=1V^*$ $I_C=1A, V_{CE}=1V^*$
Transition Frequency	f_T	100			MHz	$I_C=50mA, V_{CE}=10V$ $f=100MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$